

# S-Band, GaN/SiC, 50-Ohm RF Power Transistor

2.9 - 3.4 GHz | 250 W typ | 55% Efficiency typ | 14dB Gain typ | 50 V | 150μs Pulse Length, 10% Duty Cycle

IGT2934M250 is a high power GaN-on-SiC RF power transistor that is fully matched to  $50\Omega$  at both the input and output. It supplies a minimum of 250W of peak output power, with typically >14dB of gain and 55% efficiency. It operates from a 50V supply voltage. For optimal thermal efficiency, the transistor is housed in a metal-based package with an epoxy-sealed ceramic lid.

#### **FEATURES**

- GaN on SiC HEMT Technology
- Output Power 250W
- Fully matched to  $50\Omega$  at both input and output
- 100% RF Tested Under 150μs, 10% duty cycle pulse conditions
- RoHS and REACH Compliant

# **APPLICATIONS**

S-band Radar Systems

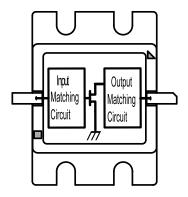


Table 1. RF Electrical Characteristics (Case temperature = 30 °C unless otherwise stated).

| Parameter               | Symbol   | Min  | Тур  | Max  | Units | Test Conditions   |  |
|-------------------------|----------|------|------|------|-------|---|--|
| Gain                    | G        | 11   | 14   | 16   | dB    |   |  |
| Drain Efficiency        | η        | 50   | 55   | 60   | %     |   |  |
| Pulse Droop             | D        | -0.8 | -0.1 | +0.2 | dB    | $P_{OUT} = 250W$<br>f = 2.9, 3.15 3.4GHz                                      |  |
| Input Return Loss       | IRL      | 7    | 18   | 25   | dB    | 150 $\mu$ s pulse length, 10% duty cycle<br>$V_{DS} = 50V$ , $I_{DS} = 52mA$  |  |
| Load Mismatch Stability | VSWR-S   | 2:1  |      |      |       |   |  |
| VSWR Withstand          | VSWR-LMT | 3:1  |      |      |       |   |  |
| Second Harmonic         |          |      | -27  |      | dBc   | P <sub>OUT</sub> = 250W<br>f = 3.15 GHz<br>150μs pulse length, 10% duty cycle |  |
| Third Harmonic          |          |      | -58  |      | dBc   | $V_{DS} = 50V$ , $I_{DS} = 52mA$  |  |

Table 2. DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

| Parameter              | Symbol         | Min  | Тур  | Max  | Units | Test Conditions               |
|------------------------|----------------|------|------|------|-------|-------------------------------|
| Gate Pinch-Off Voltage | V <sub>P</sub> | -4.0 | -3.0 | -2.5 | V     | $V_{DS} = 50V, I_{DS} = 2mA$  |
| Quiescent Gate Voltage | V <sub>Q</sub> |      | -2.4 |      | V     | $V_{DS} = 50V, I_{DS} = 52mA$ |



Table 3. Absolute Maximum Ratings (Not Simultaneous). Case temperature = 25 °C unless otherwise stated.

| Parameter                     | Symbol              | Value       | Units | Test Conditions |
|-------------------------------|---------------------|-------------|-------|-----------------|
| DC Drain-Source Voltage       | V <sub>DS</sub>     | 80          | V     |                 |
| DC Gate-Source Voltage        | $V_{gs}$            | -8 to +1.5  | V     |                 |
| DC Drain Current              | I <sub>D</sub>      | 24          | A     |                 |
| DC Gate Current               | I <sub>G</sub>      | 2.4         | mA    |                 |
| RF Input Power                | P <sub>REIN</sub>   | 12          | W     |                 |
| Operating Channel Temperature | Т <sub>сн</sub>     | -55 to +225 | °C    |                 |
| Storage Temperature           | T <sub>STG</sub>    | -55 to +150 | °C    |                 |
| Soldering Temperature         | T <sub>SOLDER</sub> | 260 for 10s | °C    |                 |

Note: Operation outside the limits given in this table may cause permanent damage to the transistor

Table 4. Thermal Resistance (Case temperature = 85 °C unless otherwise stated)

| Parameter                                   | Symbol          | Min | Тур | Max | Units | Test Conditions   |
|---|-----------------|-----|-----|-----|-------|---|
| Peak Thermal Resistance,<br>Channel to Case | R <sub>TH</sub> |     | TBD |     | °C/W  | $P_{DISS} = 205W$<br>150µs pulse length, 10% duty cycle<br>$V_{DS} = 50V$ |



# **TYPICAL RF PERFORMANCE**

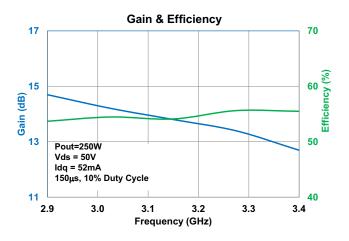


Figure 1

Figure 2

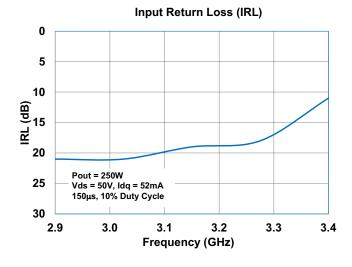
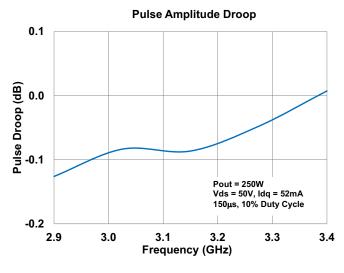


Figure 3

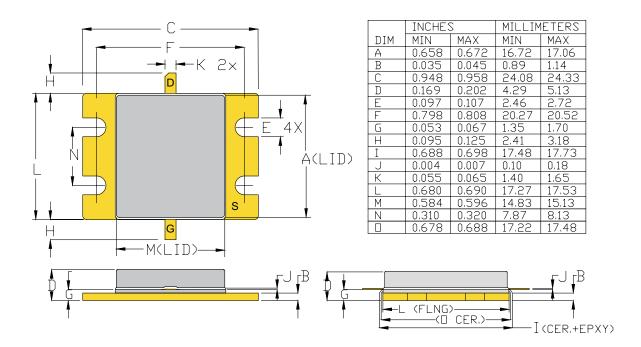


**Gain vs Output Power** 16 15 Gain (dB) 14 Vdd =50V 13 Idq = 75 mA1% duty cycle -3.4 GHz 10μs pulse length 12 50 100 150 200 250 300 350 400 450 0 **Output Power (W)** 

Figure 4



# **PACKAGE PM67A1**





# **ESD & MSL Rating**

| Parameter   | Rating | Standard               |  |  |
|---|--------|------------------------|--|--|
| ESD Human Body Model (HBM)                            | TBD    | ESDA/JEDEC JS-001-2012 |  |  |
| ESD Charged Device Model (CDM)                        | TBD    | JEDEC JESD22-C101F     |  |  |
| Moisture Sensitivty Level (MSL)  Unlimited Shelf Life |        | IPC/JEDEC J-STD-020    |  |  |

# **RoHS Compliance**

Integra Technologies, Inc declares that its GaN and LDMOS Transistor Products comply with EU Directive 2011/65/EU on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863/EU.

### **REACH Compliance**

Integra Technologies supports EU Regulation number 1907/2006 concerning the Registration, Evaluation, Authorization, and Restriction of Chemicals (REACH) as these apply to Integra semiconductor products, development tools, and shipping packaging.

In support of the REACH regulation, Integra will:

- •Inform customers and recipients of Integra product if they contain any substances that are of very high concern (SVHC) per the European Chemical Agency (ECHA) website.
- •Notify ECHA if any Integra product that contains any SVHCs which exceed guidelines for REACH chemicals by weight per part number and for total content weight per year for all products produced in or imported to the European market.
- •Cease shipments of product containing REACH Annex XIV substances until authorization has been obtained.
- Cease shipment of product containing REACH Annex XVII chemicals when restrictions apply.

Integra has evaluated its materials, BOMs, and product specifications and product and has determined that this transistor conforms to all REACH and SVHC regulations and guidelines. Integra has implemented actions and control programs that will assure continued compliance.

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**DEFINITIONS:** 

DATA SHEET STATUS

Advanced Specification - This data sheet contains Advanced specifications.

Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.

Final Specification - This data sheet contains final product specifications

MAXIMUM RATINGS Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.

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